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分機：XXXXX

參考資料目錄:

- A. Referred International Journal Papers (國際期刊)
- B. International Conference Papers (國際研討會期刊)
- C. 專利發明

A. Referred International Journal Papers (國際期刊)

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- C4. Kai-Lin Lee, **Zhi-Cheng Lee** et al., 2022, "HEMT and method of adjusting electron density of 2DEG". (Patent # 11239327)
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